

surrounds a sidewall of said second portion and said second portion does not extend above said upper surface; and

- c) a third portion overlying said second portion and, extending above and below [an] said upper surface of said insulative layer, and including a recess, wherein said first portion and said second portion are different materials.

51. (Amended) A dynamic random access memory device comprising:

a capacitor which comprises:

- a) a first portion formed in an insulative layer having an upper surface;
- b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion and said second portion does not extend above said upper surface; and
- c) a third portion overlying said second portion and, extending above and below [an] said upper surface of said insulative layer, and including a recess, wherein said first portion and said second portion are different materials.

56. (Amended) An electrode comprising:

- a) a contact formed in an insulative layer having an upper surface;
- b) a diffusion barrier portion overlying said contact, said insulative layer surrounding a sidewall of said diffusion barrier portion and said diffusion barrier portion not extending above said upper surface; and
- c) an oxidation resistant portion overlying said diffusion barrier portion and, extending above and below [an] said upper surface of said insulative layer, and including a recess, said diffusion barrier portion configured to inhibit diffusion of atoms between said contact and said oxidation resistant portion.

88. (Amended) An electrode comprising:
- a) a first portion formed in an insulative layer having an upper surface;
 - b) a second portion overlying the first portion, wherein said insulative layer surrounds a sidewall of said second portion and said second portion does not extend above the upper surface; and
 - c) a third portion overlying said second portion, extending above and below [an] said upper surface of said insulative layer, and including a recess, wherein said first portion and said second portion respectively consist essentially of polysilicon and tantalum.

Please add the following new claims:

93. An electrode comprising:
- a) a first portion formed in an insulative layer having an upper surface;
 - b) a second portion overlying the first portion and having a sidewall substantially flush with the upper surface; and
 - c) a third portion overlying the second portion, extending above and below the upper surface of the insulative layer, and including a recess, wherein the first portion and the second portion are different materials.
94. The electrode of Claim 93, wherein the second portion and the third portion are different materials.
95. The electrode of Claim 93, wherein the first portion is a silicon contact.
96. The electrode of Claim 93, wherein the second portion is a diffusion barrier layer.
97. The electrode of Claim 93, wherein the third portion is an oxidation resistant layer.

98. The electrode of Claim 93, wherein the insulative layer surrounds a sidewall of the third portion.

99. The electrode of Claim 93, wherein the insulative layer surrounds the sidewall of the second portion.

100. A dynamic random access memory device comprising:
an electrode which comprises:

- a) a first portion formed in an insulative layer having an upper surface;
- b) a second portion overlying the first portion and having a sidewall substantially flush with the upper surface; and
- c) a third portion overlying the second portion and, extending above and below the upper surface of the insulative layer, and including a recess, wherein the first portion and the second portion are different materials.

101. The electrode of Claim 100, wherein the second portion and the third portion are different materials.

102. The electrode of Claim 100, wherein the first portion and the third portion are different materials.

103. The electrode of Claim 100, wherein the first portion contacts the second portion, and the second portion contacts the third portion.

104. The electrode of Claim 100, wherein the insulative layer surrounds the sidewall of the second portion.

105. A dynamic random access memory device comprising:
a capacitor which comprises:
- a) a first portion formed in an insulative layer having an upper surface;
 - b) a second portion overlying the first portion and having a sidewall substantially flush with the upper surface; and
 - c) a third portion overlying the second portion and extending above and below the upper surface of the insulative layer, and including a recess, wherein the first portion and the second portion are different materials.
106. The electrode of Claim 105, wherein the second portion and the third portion are different materials.
107. The electrode of Claim 105, wherein the first portion and the third portion are different materials.
108. The dynamic random access memory device as specified in Claim 105, further comprising:
- a) a dielectric layer overlying the third portion; and
 - b) a cell plate electrode overlying the dielectric layer.
109. The dynamic random access memory device as specified in Claim 105 further comprising a transistor.
110. The electrode of Claim 105, wherein the first portion contacts the second portion, and the second portion contacts the third portion.
111. The electrode of Claim 105, wherein the insulative layer surrounds the sidewall of the second portion.

112. An electrode comprising:

- a) a contact formed in an insulative layer having an upper surface;
- b) a diffusion barrier portion overlying the contact and having a sidewall substantially flush with the upper surface; and
- c) an oxidation resistant portion overlying the diffusion barrier portion and, extending above and below the upper surface, and including a recess, the diffusion barrier portion configured to inhibit diffusion of atoms between the contact and the oxidation resistant portion.

113. The electrode of Claim 112, wherein the contact contacts the diffusion barrier, and the diffusion barrier portion contacts the oxidation resistant portion.

114. An electrode comprising:

- a) a first portion formed in an insulative layer having an upper surface;
- b) a second portion overlying the first portion and having a sidewall substantially flush with the upper surface;
- c) a third portion overlying the second portion, extending above and below the upper surface, and including a recess, wherein the first portion and the second portion respectively consist essentially of polysilicon and tantalum.

115. The electrode as specified in Claim 114, wherein the third portion consist essentially of platinum.

116. The electrode of Claim 114, wherein the first portion contacts the second portion, and the second portion contacts the third portion.